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PATENT

I hereby certify that on the date specified below, this correspondence is being deposited with the United States Postal Service as first-class mail in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

September 25, 2006

Date

abeggs

Alexandra Beggs

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants : Kie Y. Ahn and Leonard Forbes Attorney Docket No.: 500466.04
Patent No. : US 6,953,375 B2 Serial No. : 10/813,204
Issue Date : October 11, 2005 Filed : March 29, 2004
Title : MANUFACTURING METHOD OF A FIELD EMISSION DISPLAY HAVING
POROUS SILICON DIOXIDE INSULATING LAYER

REQUEST FOR CERTIFICATE OF CORRECTION

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Certificate
OCT 06 2006
of Correction

Sir:

A Certificate of Correction under 35 U.S.C. § 254 is respectfully requested for the above-identified patent in order to correct Patent and Trademark Office errors made during the printing of the patent. The changes in the patent needed to correct the errors are as follows:

| <u>Column, Line</u> | <u>Reads</u> | <u>Should Read</u> |
|---|------------------------------------|------------------------------------|
| Item (56), Other Publications, Stevenson Reference | "of SiO ₂ , Films Over" | --of SiO ₂ Films Over-- |
| Item (56), Other Publications, Vaudaine Reference | "technical digest of IEDM 91," | --Technical Digest of IEDM 91,-- |
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| Column 7, Line 23 | "69(7), (1996)," | --69(7) (1996)-- |
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| Column 7, Line 53 | "Part 1, Vol. 36," | --Part I, Vol. 36,-- |
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The above errors for which correction is requested under 35 U.S.C. § 254 were made in the printing of the patent or in the original application. The errors are considered sufficiently important to justify the processing of a Certificate of Correction under 35 U.S.C. § 254. A Form PTO-1050, in duplicate, is enclosed herewith.

The Commissioner is hereby authorized to charge payment of any fees associated with this communication to Deposit Account No. 50-1266. A duplicate copy of this sheet is enclosed.

OCT 11 2006

Favorable consideration of this Request is respectfully requested.

Respectfully submitted,

Date: Sept. 21, 2006

By: Edward W. Bulchis

Edward W. Bulchis, Reg. No. 26,847

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Enclosures:

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INVENTOR(S) : Kie Y. Ahn and Leonard Forbes

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Patent No. US 6,953,375 B2

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